

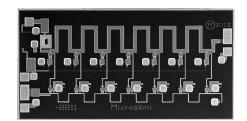
# 2-20GHz, 12.5dB Gain Low-Noise Wideband Distributed Amplifier

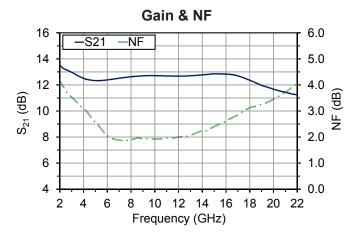
#### **Features**

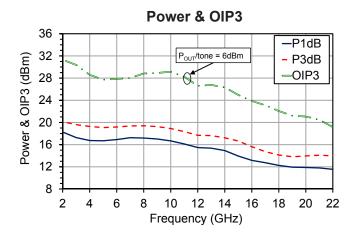
- >16.5dBm P<sub>1dB</sub> with 1.9dB NF and 12.5dB gain at 10GHz
- <2dB NF from 6-12GHz</li>
- Single supply voltage of +8V @ 50mA
- Input and Output matched to 50Ω
- 1.5mm x 2.82mm x 0.1mm die size

#### **Applications**

- Instrumentation
- Electronic warfare
- Microwave communications
- Radar







Typical Performance (CW, Typical Device, RF Probe):  $T_A = 25$ °C,  $V_{DD} = 8V$ 

Parameter	Min	Тур	Max	Units
Frequency	2	-	22	GHz
Small Signal Gain	11.3	-	13.5	dB
Noise Figure	1.9	2.5	4.0	dB
Output Power, P <sub>1dB</sub>	12	14	18	dBm
Output Power, P <sub>3dB</sub>	14	18	20	dBm
Output IP3	19	26	31	dBm
Drain Current		50		mA



**Table 1: Absolute Maximum Ratings, Not Simultaneous** 

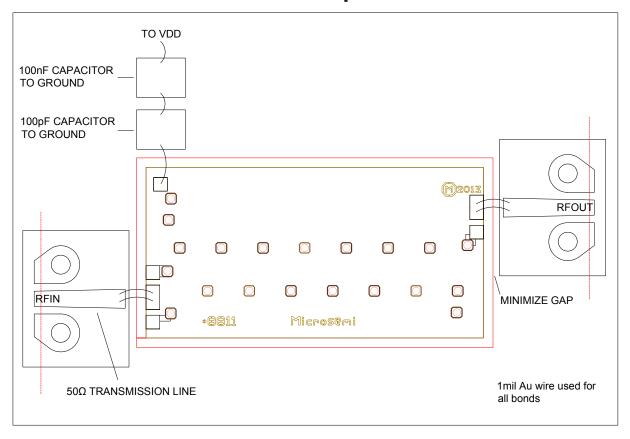
Parameter	Rating	Units
Drain Voltage (V <sub>D</sub> )	+9	V
Input Power (P <sub>IN</sub> )	24	dBm
Channel Temperature (T <sub>C</sub> )	150 <sup>1</sup>	°C
Operating Ambient Temperature (T <sub>A</sub> )	-55 to +85	°C
Storage Temperature	-65 to +150	°C
Thermal Resistance, Channel to Die Backside	40	°C/W



Table 2: Specifications (CW, 100% Test):  $T_A = 25$ °C,  $V_{DD} = 8V$ 

Parameter		Min	Max	Units
I <sub>DD</sub>	-	-	105	mA
Small Signal Gain	20GHz	9.5	-	dB
Output Power, P <sub>1dB</sub>	20GHz	9.0	-	dBm

## RF Probe Measurement Set-Up With Reference Planes<sup>2</sup>

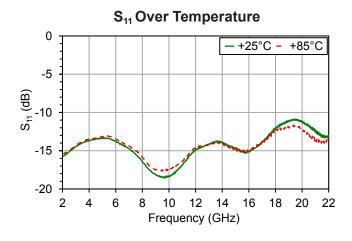


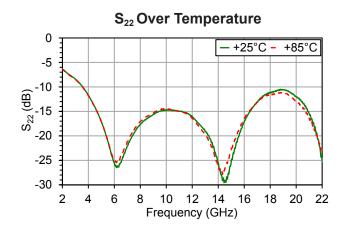
<sup>&</sup>lt;sup>2</sup> Reference planes are the same for S-parameter files downloadable on www.microsemi.com/mmics

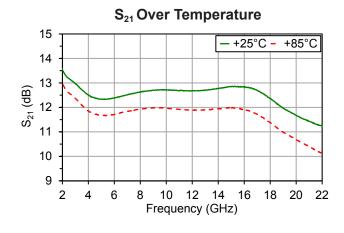
 $<sup>^{1}</sup>$  MTTF > 10 $^{8}$  hours at T<sub>C</sub> = 150 $^{\circ}$ C

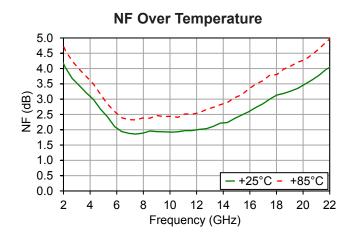


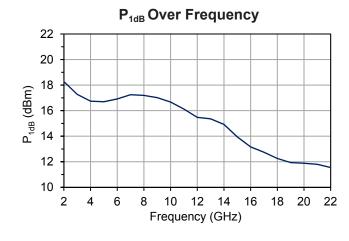
## Typical Performance, RF Probe $V_{DD}$ = 8V, $I_{DD}$ = 50mA, $T_{A}$ = 25°C unless otherwise noted

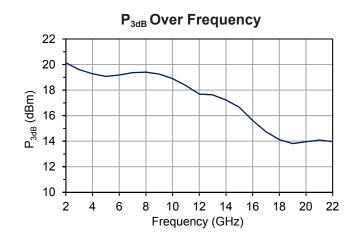






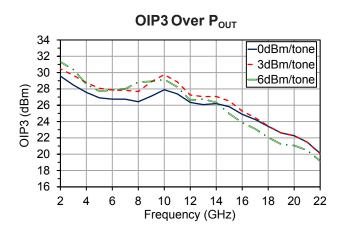




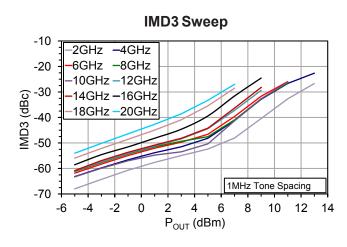




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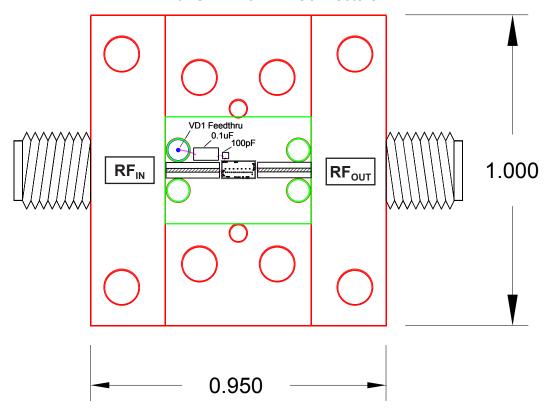






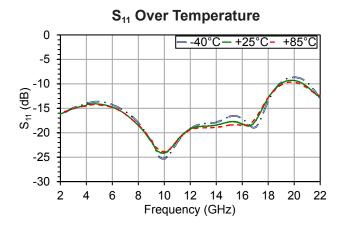
### **Connectorized Test Fixture**

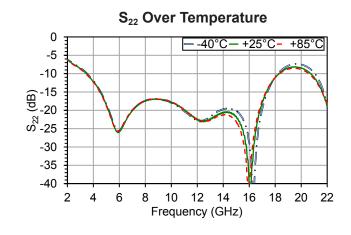
With SMK 2.92mm Connectors

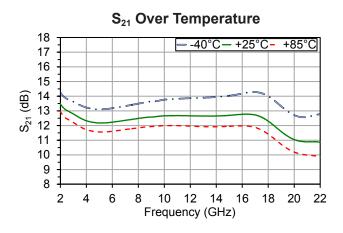


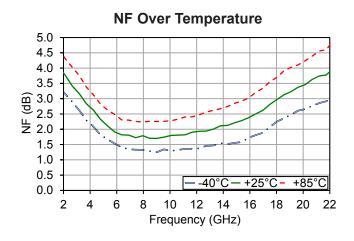


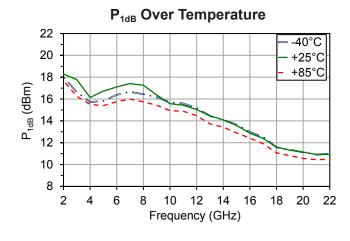
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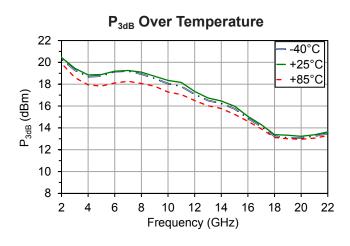










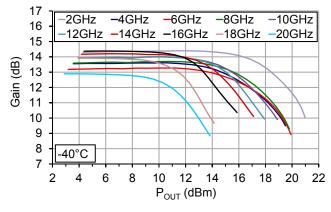




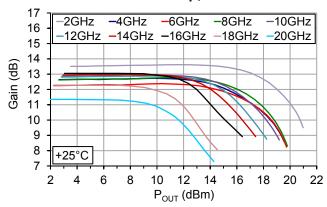
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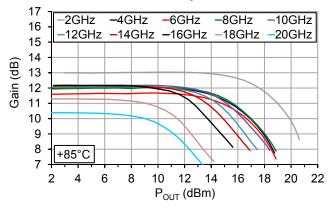
#### Power Sweep, -40°C



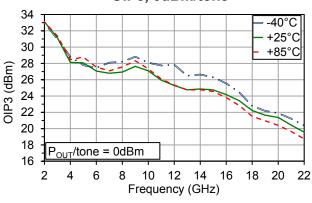
#### Power Sweep, +25°C



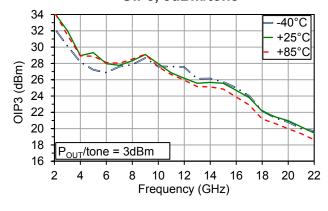
#### Power Sweep, +85°C



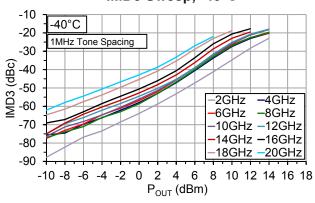
#### OIP3, 0dBm/tone



#### OIP3, 3dBm/tone



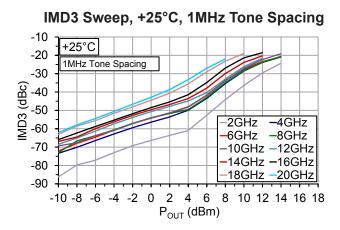
#### IMD3 Sweep, -40°C

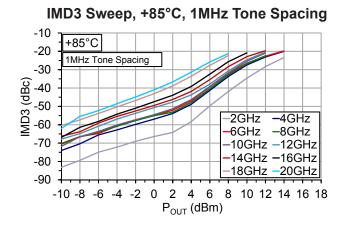


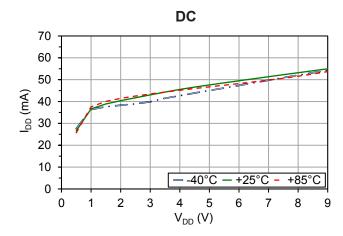


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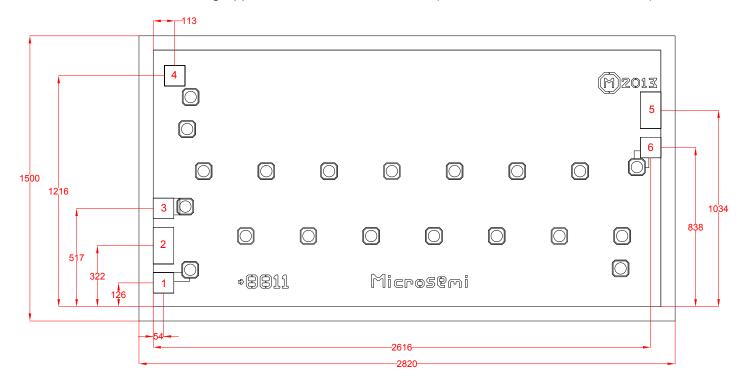






#### Chip layout showing pad locations.

All dimensions are in microns. Die thickness is 100 microns. Backside metal is gold, bond pad metal is gold. Refer to Die Handling Application Note MM-APP-0001 (visit www.microsemi.com/mmics).



**Table 3: Pad Descriptions** 

Pad #	Descrtiption	Pad Dimensions (µm)
1, 3, 6	Ground	100 x 100
2	RF <sub>IN</sub> , AC Coupled	100 x 190
5	RF <sub>OUT</sub> , AC Coupled	100 x 190
4	$V_{DD}$	100 x 100

#### Biasing

MMA003AA is a self-biased device with single positive supply. Apply  $V_{DD}$  to pad 4.





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